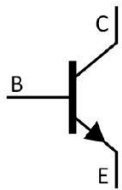


Silicon NPN transistor in a TO-18 Plastic Package.

Complementary pair with BD439.

Medium power linear and switching applications.

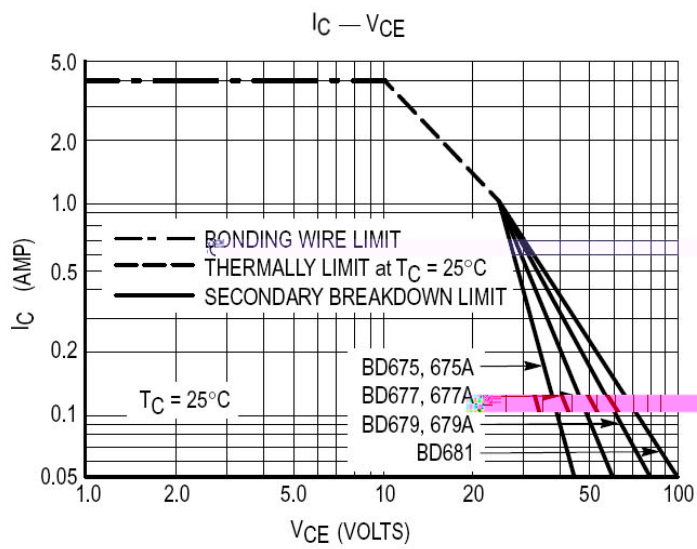
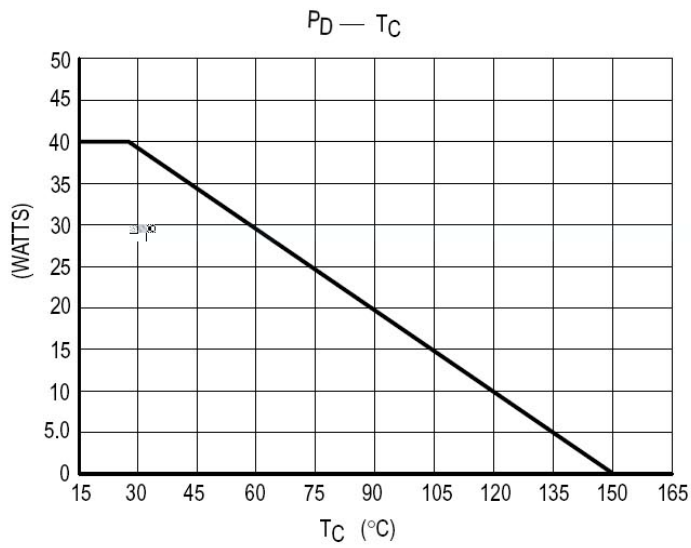


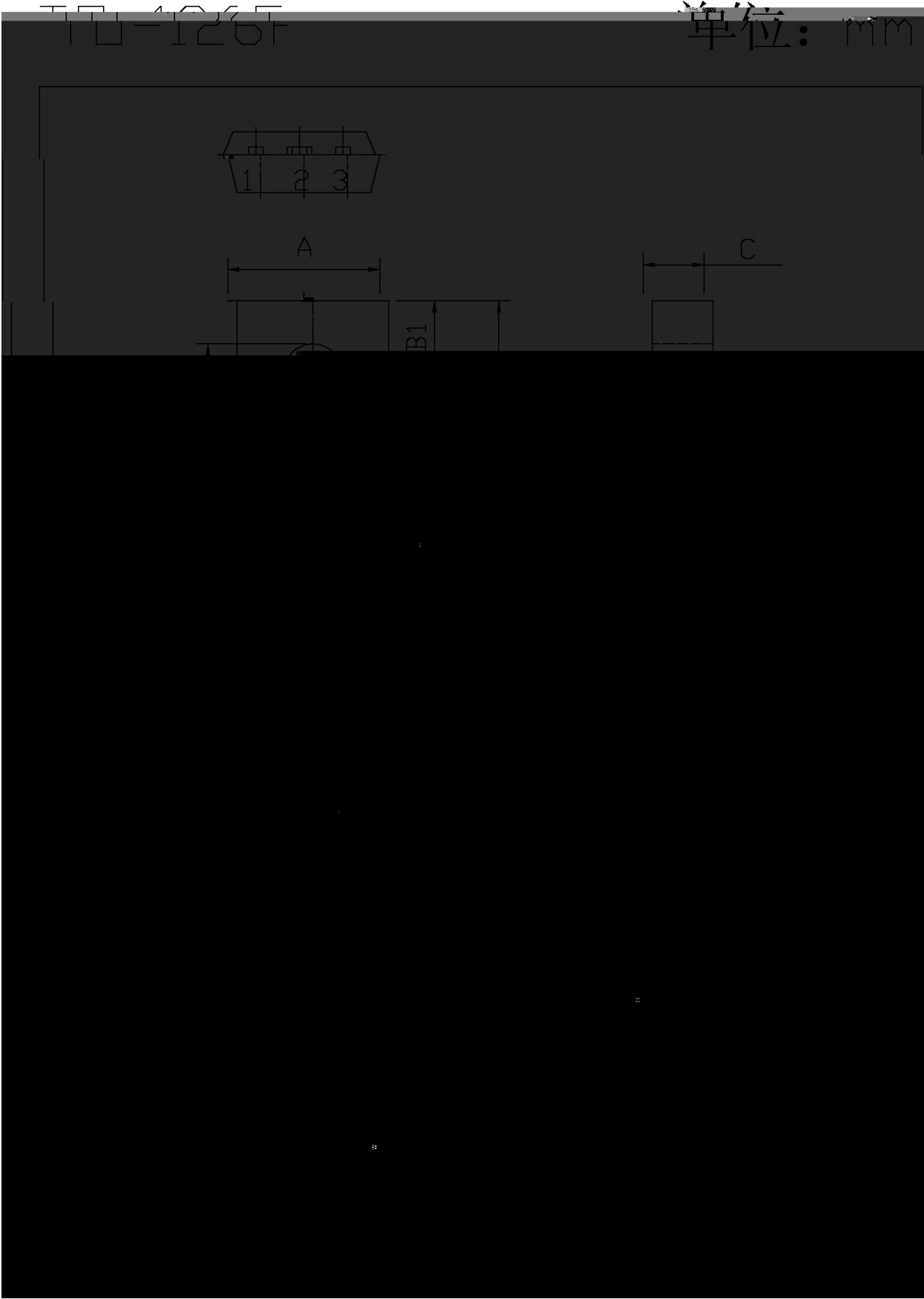
PIN1	Emitter	PIN 2	Collector	PIN 3	Base
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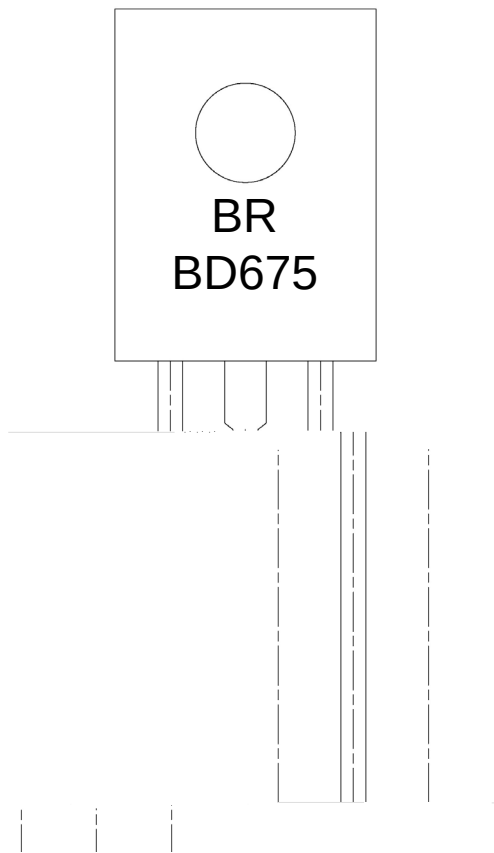
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	45	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	4.0	A
Base Current - Continuous	I_B	0.1	A
Collector Power Dissipation	P_C	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=50mA$ $I_B=0$	45			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=\text{Rated } BV_{CEO}$ $I_E=0$			0.2	mA
Collector Cut-Off Current	I_{CEO}	$V_{CE}=\text{Half Rated } V_{CEO}$ $I_B=0$			500	μA
Emitter Cut-Off Current	I_{EBO}	$V_{BE}=5.0V$ $I_C=0$			2.0	mA
DC Current Gain	h_{FE}	$V_{CE}=3.0V$ $I_C=1.5A$	750			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A$ $I_B=40mA$			2.8	V
Base to Emitter On Voltage	$V_{BE(on)}$	$I_C=2.0A$ $V_{CE}=3.0V$			2.5	V





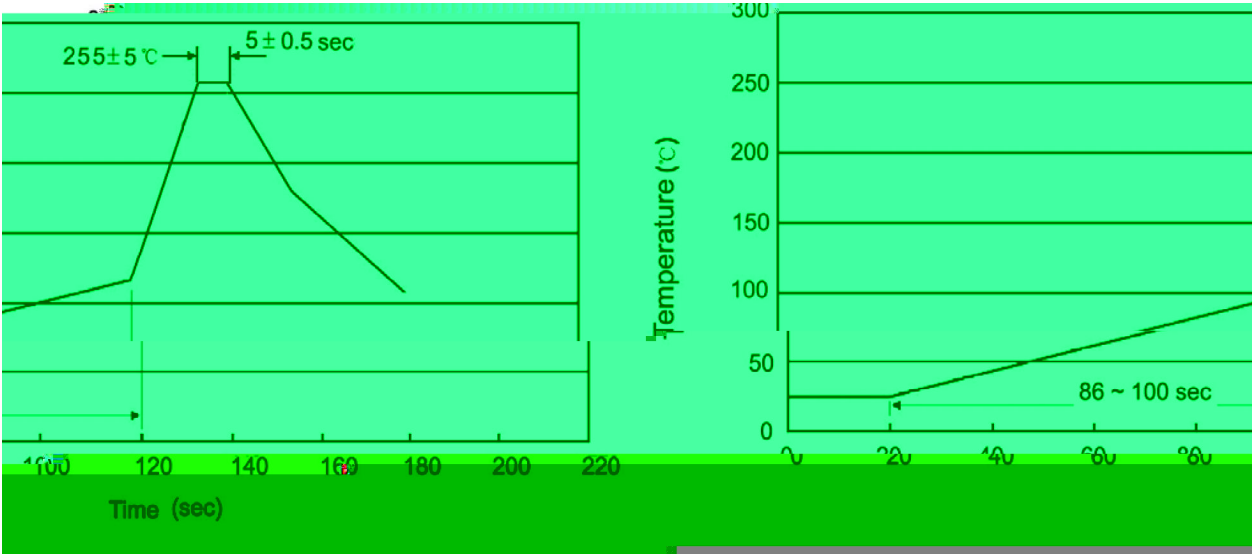


Note:

BR: Company Code

BD675: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.

Note:

1.Preheating:25~150

, Time:60~90sec.

2.Peak Temp.:255 5

, Duration:5 0.5sec.

3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱